



Data sheet acquired from Harris Semiconductor
SCHS168

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CD74HCT242, CD74HC243, CD74HCT243

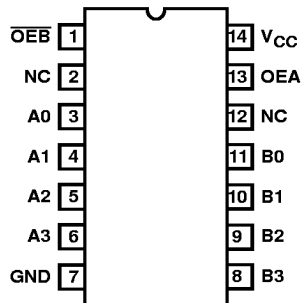
High Speed CMOS Logic Quad-Bus Transceiver with Three-State Outputs

Features

- Typical Propagation Delay (A to B, B to A) of 7ns at $V_{CC} = 5V$, $C_L = 15pF$, $T_A = 25^\circ C$
- Three-State Outputs
- Buffered Inputs
- Fanout (Over Temperature Range)
 - Standard Outputs 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range . . . $-55^\circ C$ to $125^\circ C$
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: $N_{IL} = 30\%$, $N_{IH} = 30\%$ of V_{CC} at $V_{CC} = 5V$
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility, $V_{IL} = 0.8V$ (Max), $V_{IH} = 2V$ (Min)
 - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL} , V_{OH}

Pinout

CD74HCT242, CD74HC243, CD74HCT243
(PDIP, SOIC)
TOP VIEW



Description

The Harris CD74HCT242, CD74HC243 and CD74HCT243 silicon-gate CMOS three-state bidirectional inverting and non-inverting buffers are intended for two-way asynchronous communication between data buses. They have high drive current outputs which enable high-speed operation when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuits, and have speeds comparable to low power Schottky TTL circuits. They can drive 15 LSTTL loads.

The CD74HCT242 is an inverting buffer; the CD74HC243 and CD74HCT243 are non-inverting buffers.

The states of the output enables ($\overline{OEB}$, OEA) determine both the direction of flow (A to B, B to A), and the three-state mode.

Ordering Information

PART NUMBER	TEMP. RANGE ($^\circ C$)	PACKAGE	PKG. NO.
CD74HC243E	-55 to 125	14 Ld PDIP	E14.3
CD74HC243M	-55 to 125	14 Ld SOIC	M14.15
CD74HCT243M	-55 to 125	14 Ld SOIC	M14.15

NOTES:

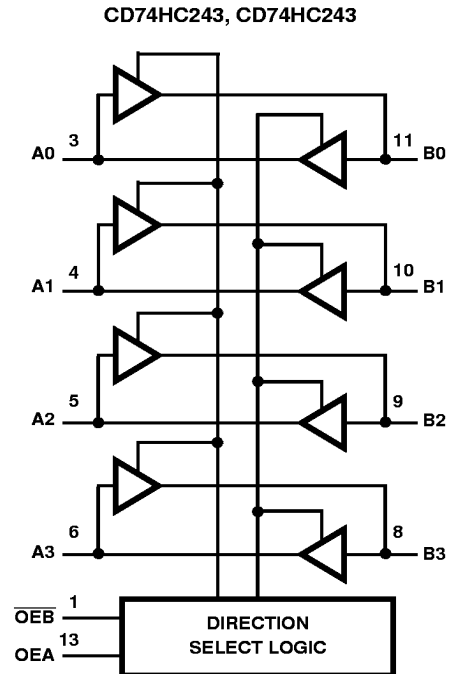
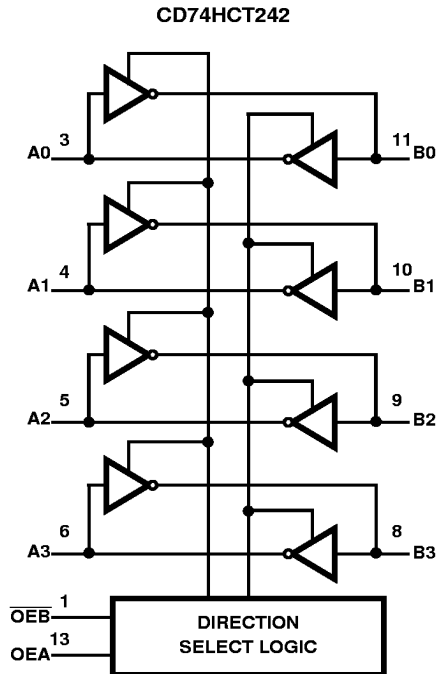
1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
2. Wafer or die for this part number is available which meets all electrical specifications. Please contact your local sales

CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures.

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Functional Diagrams



TRUTH TABLE

CONTROL INPUTS		HCT242 SERIES		HC, HCT243 SERIES	
		DATA PORT STATUS		DATA PORT STATUS	
$\overline{OEB}$	OEA	An	Bn	An	Bn
H	H	$\overline{O}$	I	O	I
L	H	Z	Z	Z	Z
H	L	Z	Z	Z	Z
L	L	I	$\overline{O}$	I	O

NOTE:

H = High Voltage Level

L = Low Voltage Level

I = Input

O = Output (Same Level as Input)

$\overline{O}$ = Output (Inversion of Input Level)

Z = High Impedance

To prevent excess currents in the High Z modes all I/O terminals should be terminated with 10k Ω to 1M Ω resistors.

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Absolute Maximum Ratings

DC Supply Voltage, V_{CC}	-0.5V to 7V
DC Input Diode Current, I_{IK}	
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$	$\pm 20mA$
DC Output Diode Current, I_{OK}	
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$	$\pm 20mA$
DC Drain Current, per Output, I_O	
For $-0.5V < V_O < V_{CC} + 0.5V$	$\pm 35mA$
DC Output Source or Sink Current per Output Pin, I_O	
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$	$\pm 25mA$
DC V_{CC} or Ground Current, I_{CC}	$\pm 70mA$

Thermal Information

Thermal Resistance (Typical, Note 3)	θ_{JA} ($^{\circ}C/W$)
PDIP Package	90
SOIC Package	175
Maximum Junction Temperature	150 $^{\circ}C$
Maximum Storage Temperature Range	-65 $^{\circ}C$ to 150 $^{\circ}C$
Maximum Lead Temperature (Soldering 10s)	300 $^{\circ}C$ (SOIC - Lead Tips Only)

Operating Conditions

Temperature Range (T_A)	-55 $^{\circ}C$ to 125 $^{\circ}C$
Supply Voltage Range, V_{CC}	
HC Types	.2V to 6V
HCT Types	.45V to 5.5V
DC Input or Output Voltage, V_I , V_O	0V to V_{CC}
Input Rise and Fall Time	
2V	1000ns (Max)
4.5V	500ns (Max)
6V	400ns (Max)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V _I (V)	I _O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V _{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V _{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads	V _{OH}	V _{IH} or V _{IL}	-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads	V _{OL}	V _{IH} or V _{IL}	6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V

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DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	± 0.1	-	± 1	-	± 1	μA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	μA
Three-State Leakage Current	I_{OZ}	V_{IL} or V_{IH}	-	6	-	-	± 0.5	-	± 0.5	-	± 10	μA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} to GND	0	5.5	-	-	± 0.1	-	± 1	-	± 1	μA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 4)	ΔI_{CC}	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA
Three-State Leakage Current	I_{OZ}	V_{IL} or V_{IH}	-	5.5	-	-	± 0.5	-	± 5.0	-	± 10	μA

NOTE:

4. For dual-supply systems theoretical worst case ($V_I = 2.4V$, $V_{CC} = 5.5V$) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
A_n, B_n	1.1
$OEA, \overline{OEB}$	0.6

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360 μA max at 25°C.

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Switching Specifications Input $t_r, t_f = 6\text{ns}$

PARAMETER	SYMBOL	TEST CONDITIONS	V _{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
HC TYPES								
Propagation Delay Data to Outputs (HC243)	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	90	115	135	ns
			4.5	-	18	23	27	ns
		C _L = 15pF	5	7	-	-	-	ns
		CL = 50pF	6	-	15	20	23	ns
Output High-Z, to High Level to Low Level	t _{PZL} , t _{PZH}	C _L = 50pF	2	-	150	190	225	ns
		CL = 50pF	4.5	-	30	38	45	ns
		CL = 15pF	5	12	-	-	-	ns
		CL = 50pF	6	-	26	33	38	ns
Output High Level, Output Low Level to High-Z	t _{PHZ} , t _{PLZ}	C _L = 50pF	2	-	150	190	225	ns
		CL = 50pF	4.5	-	30	38	45	ns
		CL = 15pF	5	12	-	-	-	ns
		CL = 50pF	6	-	26	33	38	ns
Output Transition Times	t _{TLH} , t _{THL}	C _L = 50pF	2	-	60	75	90	ns
			4.5	-	12	15	18	ns
			6	-	10	13	15	ns
Input Capacitance	C _I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C _O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (HC243) (Notes 5, 6)	C _{PD}	-	5	80	-	-	-	pF
HCT TYPES								
Propagation Delay Data to Outputs (HCT242)	t _{PLH} , t _{PHL}	C _L = 50pF	4.5	-	20	25	30	ns
		C _L = 15pF	5	8	-	-	-	ns
Propagation Delay Data to Outputs (HCT243)	t _{PLH} , t _{PHL}	C _L = 50pF	4.5	-	22	28	33	ns
		C _L = 15pF	5	9	-	-	-	ns
Output High-Z to High Level to Low Level	t _{PZH} , t _{PZL}	C _L = 50pF	4.5	-	34	43	51	ns
		C _L = 15pF	5	14	-	-	-	ns
Output High Level, Output Low Level to High-Z	t _{PHZ} , t _{PLZ}	C _L = 50pF	4.5	-	35	44	53	ns
		C _L = 15pF	5	14	-	-	-	ns
Output Transition Times	t _{TLH} , t _{THL}	C _L = 50pF	4.5	-	12	15	18	ns
Input Capacitance	C _I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C _O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 5, 6)	C _{PD}	HCT242	5	90	-	-	-	pF
		HCT243	5	91	-	-	-	pF

NOTES:

5. C_{PD} is used to determine the dynamic power consumption, per channel.
6. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, f_O = Output Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms

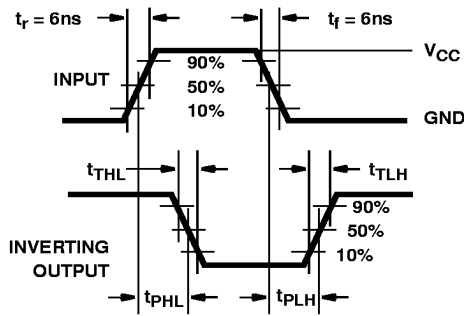


FIGURE 1. HC AND HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

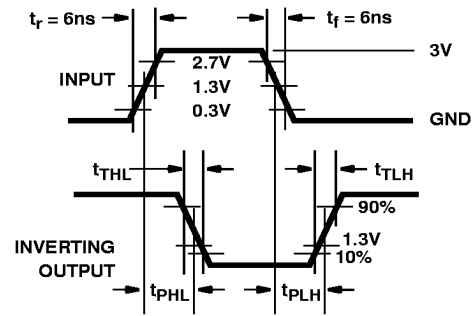


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

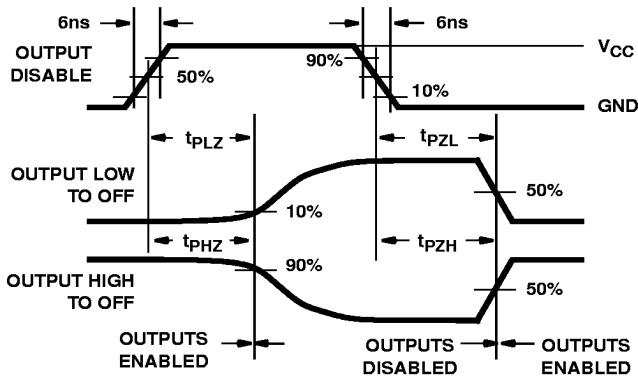


FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM

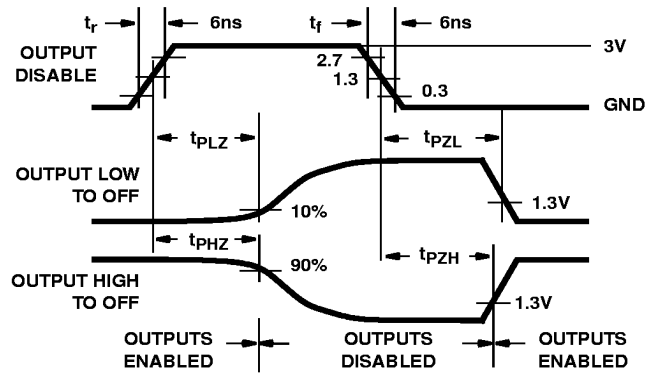
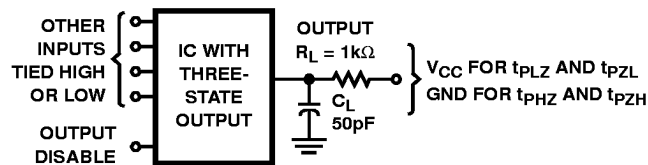


FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output $R_L = 1k\Omega$ to V_{CC} , $C_L = 50pF$.

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT